

Description

The NTD24N06 uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})},$ low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

V_{DS} = 60V I_D =20 A

 $R_{DS(ON)} < 32m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

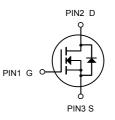
Package Marking and Ordering Information

| Product ID | Pack | Brand | Qty(PCS) |
|------------|-----------|------------|----------|
| NTD24N06 | TO-252-2L | HXY MOSFET | 2500 |

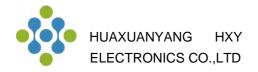
Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

| Symbol | Parameter | Rating | Units | |
|-------------------------|--|---|-------|--|
| Vds | Drain-Source Voltage | 60 | V | |
| Vgs | Gate-Source Voltage ±20 | | V | |
| I⊳@Tc=25°C | Continuous Drain Current, V _{GS} @ 10V ¹ | 20 | А | |
| I₀@Tc=100°C | Continuous Drain Current, V _{GS} @ 10V ¹ | Continuous Drain Current, V _{GS} @ 10V ¹ 10 | | |
| Ідм | Pulsed Drain Current ² | 80 | А | |
| EAS | Single Pulse Avalanche Energy ³ | ngle Pulse Avalanche Energy ³ 38 | | |
| P₀@T _C =25°C | Total Power Dissipation ⁴ | 34.7 | W | |
| Тѕтс | Storage Temperature Range -55 to 150 | | °C | |
| TJ | Operating Junction Temperature Range | -55 to 150 | °C | |





N-Channel MOSFET



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

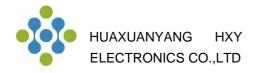
| Parameter | | Symbol | Test Conditions | Min. | Тур. | Max. | Unit |
|---|------------------------|----------------------|---|----------|------|------|------|
| Static Characteristics | | | | | 1 | 1 | |
| Drain-Source Breakdown Voltage | | V _{(BR)DSS} | V_{GS} = 0V, I _D = 250µA | 60 | - | - | V |
| Gate-Body Leakage Curren | t | lgss | $V_{DS} = 0V, V_{GS} = \pm 20V$ | - | - | ±100 | nA |
| Zero Gate Voltage Drain Current | TJ=25℃ | - I _{DSS} | V _{DS} = 60V, V _{GS} = 0V | - | - | 1 | μA |
| | TJ=100℃ | | | - | - | 100 | |
| Gate-Threshold Voltage | | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 1.2 | 1.7 | 2.5 | V |
| Drain-Source on-Resistance ⁴ | | _ | V _{GS} = 10V, I _D = 10A | - | 25 | 32 | |
| | | RDS(on) | V _{GS} = 4.5V, I _D = 5A | - | 31.5 | 40 | mΩ |
| Forward Transconductance ⁴ | | g fs | V _{DS} = 5V, I _D = 10A | - | 15.5 | - | S |
| Dynamic Characteristic | :S ⁵ | | | | | • | • |
| Input Capacitance | Input Capacitance | | | - | 1355 | - | pF |
| Output Capacitance | | Coss | V _{DS} = 30V, V _{GS} =0V, f =1MHz | - | 60 | - | |
| Reverse Transfer Capacitance | | Crss | - | - | 49 | - | |
| Gate Resistance | | Rg | f =1MHz | - | 1.2 | - | Ω |
| Switching Characteristi | CS ⁵ | | | | | | • |
| Total Gate Charge | | Qg | | - | 22 | - | nC |
| Gate-Source Charge | | Q _{gs} | V _{GS} = 10V, V _{DD} = 30V, I _D = 10A | - | 4.2 | - | |
| Gate-Drain Charge | | Q _{gd} | | - | 6.9 | - | |
| Turn-on Delay Time | | t _{d(on)} | V _{GS} =10V, V _{DD} = 30V, | - | 6.4 | - | |
| Rise Time | | tr | | - | 15.3 | - | |
| Turn-off Delay Time | | t _{d(off)} | R _G = 3Ω, I _D = 10A | - | 25 | - | ns |
| Fall Time | | t _f | | - | 7.6 | - | |
| Body Diode Reverse Recovery Time | | trr | | - | 26 | - | ns |
| Body Diode Reverse Recovery Charge | | Qrr | I _F =10A, dI _F /dt=100A/µs | - | 45 | - | nC |
| Drain-Source Body Dio | de Charactei | istics | | I | 1 | 1 | 1 |
| Diode Forward Voltage ⁴ | | Vsd | I _S = 10A, V _{GS} = 0V | - | - | 1.2 | V |
| Continuous Source Current | Tc=25℃ | Is | _ | _ | _ | 20 | Α |

Notes:

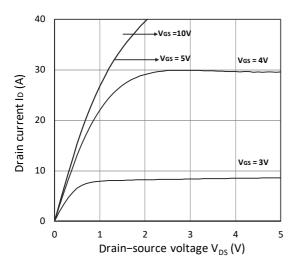
1. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}\text{=}150^\circ\text{C}$

- 2. The EAS data shows Max. rating . The test condition is $V_{\text{DD}}\text{=}25V,\,V_{\text{GS}}\text{=}10V,\,L\text{=}0.4\text{mH},\,I_{\text{AS}}\text{=}14\text{A}$
- 3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 4. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.

5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics





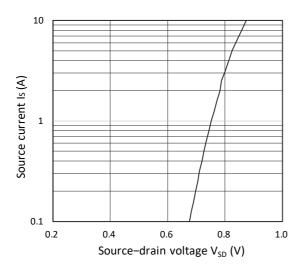


Figure 3. Forward Characteristics of Reverse

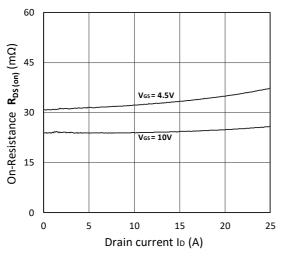


Figure 5. $R_{\text{DS}(\text{ON})}$ vs. I_{D}

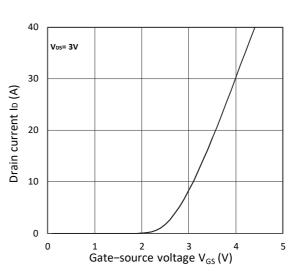
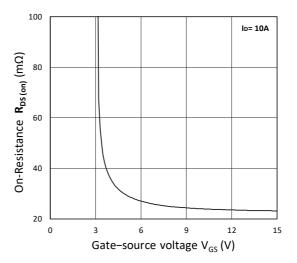


Figure 2. Transfer Characteristics





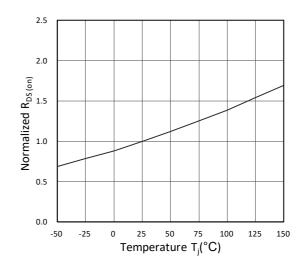
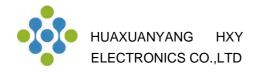


Figure 6. Normalized R_{DS(on)} vs. Temperature



N-Channel Enhancement Mode MOSFET

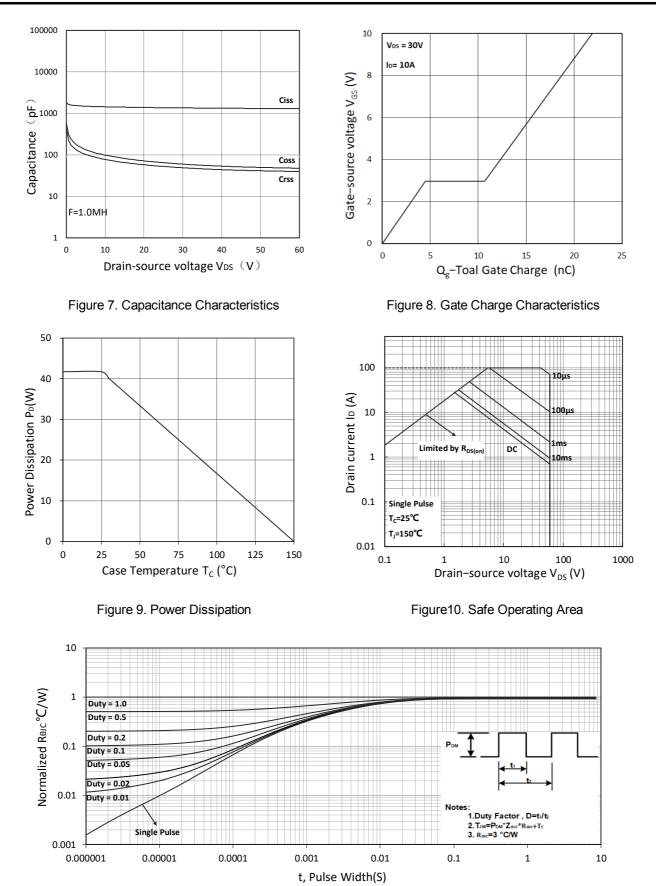
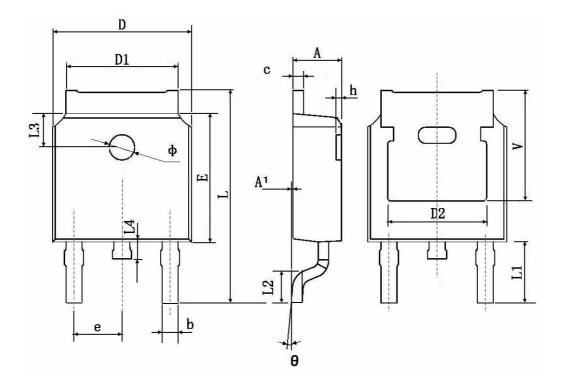


Figure 11. Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | | |
|--------|---------------------------|--------|----------------------|-------|--|
| | Min. | Max. | Min. | Max. | |
| A | 2.200 | 2.400 | 0.087 | 0.094 | |
| A1 | 0.000 | 0.127 | 0.000 | 0.005 | |
| b | 0.660 | 0.860 | 0.026 | 0.034 | |
| с | 0.460 | 0.580 | 0.018 | 0.023 | |
| D | 6.500 | 6.700 | 0.256 | 0.264 | |
| D1 | 5.100 | 5.460 | 0.201 | 0.215 | |
| D2 | 0.483 TYP. | | 0.190 TYP. | | |
| E | 6.000 | 6.200 | 0.236 | 0.244 | |
| е | 2.186 | 2.386 | 0.086 | 0.094 | |
| L | 9.800 | 10.400 | 0.386 | 0.409 | |
| L1 | 2.900 TYP. | | 0.114 TYP. | | |
| L2 | 1.400 | 1.700 | 0.055 | 0.067 | |
| L3 | 1.600 TYP. | | 0.063 TYP. | | |
| L4 | 0.600 | 1.000 | 0.024 | 0.039 | |
| Φ | 1.100 | 1.300 | 0.043 | 0.051 | |
| θ | 0 ° | 8° | 0° | 8° | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| V | 5.350 TYP. | | 0.211 TYP. | | |



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